## AUTOMOTIVE, $125^{\circ} \mathrm{C}$ OPERATION, 36 V INPUT, <br> STEP-UP / FLYBACK SWITCHING REGULATOR CONTROLLER

This IC is a step-up / flyback switching regulator controller developed using high withstand voltage CMOS process technologies.
Its wide input operating range of 3.0 V to 36 V makes it suitable for powering automotive start-stop systems and emergency battery backup systems. When this IC is used to configure a converter and the output voltage (Vout) of the converter is applied to the VIN pin in a bootstrap configuration, the input voltage can be extended below the operating input voltage range after startup.
This IC contributes to system space saving as it adopted suitable packages for high-density mounting like small-sized HSNT-8(2030), can operate at very high switching frequencies, and the peripheral parts can be made compact.
An overcurrent protection circuit protects the IC and the coil from excessive load current, and a thermal shutdown circuit prevents damage from heat generation.

ABLIC Inc. offers FIT rate calculated based on actual customer usage conditions in order to support customer functional safety design.
For more information regarding our FIT rate calculation, contact our sales representatives.
Caution This product can be used in vehicle equipment and in-vehicle equipment. Before using the product for these purposes, it is imperative to contact our sales representatives.

## ■ Features

- Input voltage:
3.0 V to 36.0 V
- Low voltage operation after startup (bootstrap configuration)
- Control system:
- FB pin voltage accuracy:
- Oscillation frequency:
- Overcurrent protection function:
- Thermal shutdown function:
- Short-circuit protection function:
- Soft-start function:
- Under voltage lockout function (UVLO):
- Input and output capacitors:
- Operation temperature range:
- Lead-free (Sn 100\%), halogen-free
- Withstand 45 V load dump
- AEC-Q100 in process**

Current mode
$\pm 1.5 \%$
2.2 MHz typ., 400 kHz typ.

Pulse-by-pulse method
$170^{\circ} \mathrm{C}$ typ. (detection temperature)
Hiccup control, Latch control
5.8 ms typ.
2.75 V typ. (detection voltage)

Ceramic capacitor compatible
$\mathrm{Ta}=-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$

## Applications

- Automotive and industrial step-up flyback converters
- Automotive start-stop systems
- Emergency battery backup systems
- Automotive LED lamps
- For automotive use (engine, transmission, suspension, ABS, related-devices for EV / HEV / PHEV, etc.)


## - Packages

- HTMSOP-8
( $4.0 \mathrm{~mm} \times 2.9 \mathrm{~mm} \times \mathrm{t} 0.8 \mathrm{~mm}$ max.)
- HSNT-8(2030)
( $3.0 \mathrm{~mm} \times 2.0 \mathrm{~mm} \times \mathrm{t} 0.5 \mathrm{~mm}$ max.)
*1. Contact our sales representatives for details.


## ■ Typical Application Circuit



## Efficiency



Block Diagram

*1. Parasitic diode
Figure 1

## ■ AEC-Q100 in Process

Contact our sales representatives for details of AEC-Q100 reliability specification.

## ■ Product Name Structure

1. Product name

*1. Refer to the tape drawing.
*2. Refer to "2. Function list of product types".
2. Function list of product types

Table 1

| Product Type | Oscillation Frequency | Short-circuit Protection Function |
| :---: | :---: | :--- |
| A | 2.2 MHz | Hiccup control |
| B | 2.2 MHz | Latch control |
| C | 400 kHz | Hiccup control |
| D | 400 kHz | Latch control |

3. Packages

Table 2 Package Drawing Codes

| Package Name | Dimension | Tape | Reel | Land |
| :--- | :---: | :---: | :---: | :---: |
| HTMSOP-8 | FP008-A-P-SD | FP008-A-C-SD | FP008-A-R-SD | FP008-A-L-SD |
| HSNT-8(2030) | PP008-A-P-SD | PP008-A-C-SD | PP008-A-R-SD | PP008-A-L-SD |

## ■ Pin Configurations

1. HTMSOP-8

Table 3


| Pin No. | Symbol |  |
| :---: | :--- | :--- |
| 1 | EN | Enable pin |
| 2 | COMP | Error amplifier circuit output pin |
| 3 | FB | Feedback pin |
| 4 | VIN | Power supply pin |
| 5 | VREG $^{* 2}$ | Internal power supply pin |
| 6 | GATE | Gate drive output pin |
| 7 | VSS | GND pin |
| 8 | SENSE | Current detection input pin |

Figure 2
*1. Connect the heat sink of backside at shadowed area to the board, and set electric potential GND. However, do not use it as the function of electrode.
*2. The VREG pin cannot supply load current outside.
2. HSNT-8(2030)

Table 4


Bottom view


| Pin No. | Symbol | Description |
| :---: | :--- | :--- |
| 1 | EN | Enable pin |
| 2 | COMP | Error amplifier circuit output pin |
| 3 | FB | Feedback pin |
| 4 | VIN | Power supply pin |
| 5 | VREG $^{* 2}$ | Internal power supply pin |
| 6 | GATE | Gate drive output pin |
| 7 | VSS | GND pin |
| 8 | SENSE | Current detection input pin |

Figure 3
*1. Connect the heat sink of backside at shadowed area to the board, and set electric potential GND However, do not use it as the function of electrode.
*2. The VREG pin cannot supply load current outside.

## ■ Absolute Maximum Ratings

## Table 5

(Unless otherwise specified: $\mathrm{Ta}=+25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{ss}}=0 \mathrm{~V}$ )

| Item | Symbol | Absolute Maximum Ratings | Unit |
| :---: | :---: | :---: | :---: |
| VIN pin voltage | V IN | $\mathrm{V}_{\text {ss }}-0.3$ to Vss +45 | V |
| EN pin voltage | $\mathrm{V}_{\text {EN }}$ | $\mathrm{V}_{\text {Ss }}-0.3$ to $\mathrm{V}_{\text {Ss }}+45$ | V |
| FB pin voltage | $V_{\text {FB }}$ | $\mathrm{V}_{\text {SS }}-0.3$ to $\mathrm{V}_{\text {REG }}+0.3 \leq \mathrm{V}_{\text {SS }}+6.0$ | V |
| VREG pin voltage | $V_{\text {Reg }}$ | $\mathrm{V}_{\text {ss }}-0.3$ to $\mathrm{V}_{\text {In }}+0.3 \leq \mathrm{V}_{\text {ss }}+6.0$ | V |
| GATE pin voltage | VGate | $\mathrm{V}_{\text {SS }}-0.3$ to $\mathrm{V}_{\text {REG }}+0.3 \leq \mathrm{V}_{\text {SS }}+6.0$ | V |
| COMP pin voltage | $V_{\text {comp }}$ | $\mathrm{V}_{\text {SS }}-0.3$ to $\mathrm{V}_{\text {REG }}+0.3 \leq \mathrm{V}_{\text {SS }}+6.0$ | V |
| SENSE pin voltage | V ${ }_{\text {endse }}$ | $\mathrm{V}_{\text {SS }}-0.3$ to $\mathrm{V}_{\text {REG }}+0.3 \leq \mathrm{V}_{\text {SS }}+6.0$ | V |
| Junction temperature | $\mathrm{T}_{\mathrm{j}}$ | -40 to +150 | ${ }^{\circ} \mathrm{C}$ |
| Operation ambient temperature | Topr | -40 to +125 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | $\mathrm{T}_{\text {stg }}$ | -40 to +150 | ${ }^{\circ} \mathrm{C}$ |

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

## ■ Thermal Resistance Value

Table 6

| Item | Symbol | Condition |  | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Junction-to-ambient thermal resistance*1 | $\theta_{\mathrm{JA}}$ | HTMSOP-8 | Board A | - | 159 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board B | - | 113 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board C | - | 39 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board D | - | 40 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board E | - | 30 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  | HSNT-8(2030) | Board A | - | 181 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board B | - | 135 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board C | - | 40 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board D | - | 42 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  | Board E | - | 32 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

*1. Test environment: compliance with JEDEC STANDARD JESD51-2A
Remark Refer to "■ Power Dissipation" and "Test Board" for details.

## ■ Electrical Characteristics

Table 7
$\left(\mathrm{V}_{\mathrm{IN}}=12 \mathrm{~V}, \mathrm{~T}_{\mathrm{j}}=-40^{\circ} \mathrm{C}\right.$ to $+150^{\circ} \mathrm{C}$ unless otherwise specified)

| Item | Symbol | Condition | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Operating input voltage | VIN | - | 3.0 | - | 36.0 | V |
| Current consumption during shutdown | Isss | V EN $=0 \mathrm{~V}$ | - | 0.1 | 5.0 | $\mu \mathrm{A}$ |
| Current consumption during switching off | Iss | $\mathrm{V}_{\mathrm{FB}}=0.82 \mathrm{~V}$ | - | 60 | 120 | $\mu \mathrm{A}$ |
| UVLO detection voltage | VuvLo- | VREG pin voltage | 2.55 | 2.75 | 2.95 | V |
| UVLO release voltage | Vuvlo+ | VREG pin voltage | 2.65 | 2.85 | 3.05 | V |
| FB pin voltage | $\mathrm{V}_{\text {FB }}$ | - | 0.788 | 0.800 | 0.812 | V |
| FB pin current | IfB | $\mathrm{V}_{\mathrm{FB}}=1.0 \mathrm{~V}$ | -0.06 | - | 0.06 | $\mu \mathrm{A}$ |
| Error amplifier transconductance | gm | - | - | 220 | - | $\mu \mathrm{S}$ |
| Oscillation frequency | fosc | A / B type | 1.98 | 2.2 | 2.42 | MHz |
|  |  | C / D type | 360 | 400 | 440 | kHz |
| Minimum ON time | ton_min | - | - | 45 | - | ns |
| Maximum duty ratio | MaxDuty | A / B type | 82 | 88 | 94 | \% |
|  |  | C / D type | 91 | 95 | 99 | \% |
| Soft-start wait time | tssw | Time until Vout starts rising, $C_{\text {REG }}=1 \mu \mathrm{~F}$ | 0.15 | 0.37 | 0.70 | ms |
| Soft-start time | tss | Time until $\mathrm{V}_{\text {FB }}$ reaches $90 \%$ after it starts rising | 3.0 | 5.8 | 8.5 | ms |
| GATE pin ON-resistance | Ronh | Output is "H", IGATE $=50 \mathrm{~mA}$ | - | 1.5 | 3.0 | $\Omega$ |
|  | Ronl | Output is "L", $\mathrm{I}_{\text {GATE }}=-50 \mathrm{~mA}$ | - | 1.0 | 2.0 | $\Omega$ |
| Overcurrent protection detection voltage | VıIM | - | 0.128 | 0.14 | 0.152 | V |
| VREG pin output voltage | $V_{\text {REG }}$ | - | - | 5.0 | - | V |
| Thermal shutdown detection temperature | Tsd | Junction temperature | - | 170 | - | ${ }^{\circ} \mathrm{C}$ |
| Thermal shutdown release temperature | TSR | Junction temperature | - | 150 | - | ${ }^{\circ} \mathrm{C}$ |
| High level input voltage | VSH | EN pin | 2.0 | - | - | V |
| Low level input voltage | VSL | EN pin | - | - | 0.8 | V |
| High level input current | Ish | EN pin, $\mathrm{V}_{\text {EN }}=2.0 \mathrm{~V}$ | - | - | 1 | $\mu \mathrm{A}$ |
| Low level input current | ISL | EN pin, $\mathrm{V}_{\text {en }}=0 \mathrm{~V}$ | -0.5 | - | 0.5 | $\mu \mathrm{A}$ |

## - Operation

## 1. Overview of operation

This IC adopts the current mode control. By comparing the current feedback signal which has slope compensation added to the current flows through SENSE resistor with the output signal of error amplifier, the duty ratio of the GATE pin is determined. Using the negative feedback loop configured, the error amplifier output signal is maintained at the value that $\mathrm{V}_{\mathrm{REF}}$ and FB pin voltage $\left(\mathrm{V}_{\mathrm{FB}}\right)$ will be equalized.

## 2. Inductor current operating mode

In converters that use diodes as rectifier elements, the inductor current ( I ) shifts between Discontinuous Current Mode (DCM) and Continuous Current Mode (CCM), depending on the load current (lout).
The lout when the inductor current is exactly zero during the switching cycle is the boundary mode between the discontinuous and continuous current modes. The lout at this time is shown below. For details, refer to Figure 4 to Figure 6.

$$
\text { loUT }=\frac{\mathrm{V}_{\text {IN }}{ }^{2}}{2 \times \mathrm{L} \times \mathrm{V}_{\text {OUT }}}\left(1-\frac{\mathrm{V}_{\text {IN }}}{\mathrm{V}_{\text {OUT }}}\right) T
$$


*1. Vsw is the voltage at the point (switching node) where the step-up switching regulator circuit, FET, and diode are connected, which is a square wave.

The duty cycle ( $\mathrm{D}_{\mathrm{dcm}}$ ) in discontinuous current mode operation is shown in the equation below. $\mathrm{D}_{\mathrm{dcm}}$ varies significantly with load changes.

$$
D_{\mathrm{dcm}}=\frac{\sqrt{2 \times \mathrm{L} \times \text { lout } \times\left(\mathrm{Vout}+\mathrm{V}_{\mathrm{F}}-\mathrm{V}_{\text {IN }}\right) \times \text { fosc }}}{\mathrm{V}_{\text {IN }}}
$$

And the duty cycle ( $\mathrm{D}_{\mathrm{ccm}}$ ) in continuous current mode operation is shown in the equation below. The input and output voltages determine $\mathrm{D}_{\mathrm{ccm}}$.

$$
\mathrm{D}_{\mathrm{ccm}}=1-\frac{\mathrm{V}_{\mathrm{IN}}}{\mathrm{~V}_{\mathrm{OUT}}+\mathrm{V}_{\mathrm{F}}}
$$

## Remark L:

Load current [A]
VIN: Input voltage [V]
Vout: Output voltage [V]
$V_{F}: \quad$ Diode forward voltage [V]
fosc: Oscillation frequency [Hz]
$\mathrm{T}: \quad$ Period [s]

## 3. Minimum ON time

When the external FET M1 in Figure 1 on "■ Block Diagram", is turned on, this IC starts switching at high-speed generating high-frequency spike noise in the inductor current detection resistor (RSENSE). Normally, a slope voltage proportional to the inductor current value is input to the SENSE pin, and the IC's internal latch circuit is reset to the desired voltage value. If there is any spike noise, the occurrence of the noise will reset the latch incorrectly. To prevent such malfunctions, a blank time is set so that a reset is not triggered even if M1 is turned on. This blank time is defined as the minimum ON time (ton_min).

## 4. PWM / PFM switching control

This IC automatically switches between pulse width modulation method (PWM) and pulse frequency modulation method (PFM) according to the load current. PFM control is selected when under light load, and the pulse will skip according to the load current. Pulse skips will occur when the following conditions are met.

Ddcm $<$ ton_min $\times$ fosc
Pulse skipping reduces self-current consumption and improves efficiency at light loads.

## 5. Under voltage lockout function (UVLO)

This IC has a built-in UVLO circuit to prevent the IC from malfunctioning due to a transient status at power-on or a momentary drop in the supply voltage. When UVLO status is detected, the GATE pin is pulled down. For this reason, switching operation will stop. The soft-start function is reset if UVLO status is detected once and is restarted by releasing the UVLO status.
Note that the other internal circuits operate normally, and the status is different from the disabled status.
Also, there is a hysteresis width for avoiding malfunctions due to generation of noise etc. in the input voltage.

## 6. Output voltage settings

Set the output voltage (Vout) by connecting voltage setting resistors $\mathrm{R}_{\text {FB1 }}$ and $\mathrm{R}_{\text {FB2 }}$ to the FB pin as shown in the equation below.

$$
V_{\text {OUT }}=V_{F B} \times \frac{R_{F B 1}+R_{F B 2}}{R_{F B 2}}
$$

## 7. EN pin

This pin starts and stops switching operation. When the EN pin is set to "L", the operation of all internal circuits is stopped, reducing current consumption. When not using the EN pin, connect it to the VIN pin. Since the EN pin is neither pulled down nor pulled up internally, do not use it in the floating status. The structure of the EN pin is shown in Figure 7, and the clamp circuit is internally connected.

Table 8

| EN Pin | Internal Circuit | GATE |
| :--- | :--- | :--- |
| "H" | Enable (normal operation) | Switching operation |
| "L" | Disable (standby) | Pulled down to Vss |



Figure 7

## 8. Thermal shutdown function

This IC has a built-in thermal shutdown circuit to limit overheating. When the junction temperature increases to $170^{\circ} \mathrm{C}$ typ., the thermal shutdown circuit becomes the detection status, and the switching operation is stopped. When the junction temperature decreases to $150^{\circ} \mathrm{C}$ typ., the thermal shutdown circuit becomes the release status, and the switching operation is restarted.
If the thermal shutdown circuit becomes the detection status due to self-heating, the switching operation is stopped and output voltage (Vout) decreases. For this reason, the self-heating is limited and the temperature of the IC decreases. The thermal shutdown circuit becomes release status when the temperature of the IC decreases, and the switching operation is restarted, thus the self-heating is generated again. Repeating this procedure makes the waveform of Vout into a pulse-like form. Note that the product may suffer physical damage such as deterioration if the above phenomenon occurs continuously. Switching operation stopping and starting can be stopped by either setting the EN pin to "L", lowering the output current (lоит) to reduce internal power consumption, or decreasing the ambient temperature.

Table 9

| Thermal Shutdown Circuit | GATE |
| :--- | :--- |
| Release: $150^{\circ} \mathrm{C}$ typ. ${ }^{* 1}$ | Switching operation |
| Detection: $170^{\circ} \mathrm{C}$ typ. ${ }^{* 1}$ | Pulled down to $\mathrm{V}_{\mathrm{ss}}$ |

*1. Junction temperature

## 9. Overcurrent protection function

The overcurrent protection circuit monitors the current that flows through the external FET and limits current to prevent thermal destruction of the IC due to an overload, magnetic saturation in the inductor, etc.
When overcurrent flows through the external FET and the potential difference between the SENSE pin and GND exceeds the overcurrent protection detection voltage ( $\mathrm{V}_{\mathrm{LIM}}$ ) ( 0.14 V typ.), the external FET is turned off. It is turned back on when the next switching cycle starts. If the potential difference between the SENSE pin and GND remains above $\mathrm{V}_{\text {Lim, }}$ the external FET is turned off again, and this sequence of operations is repeated.
However, when the current flowing through the external FET decreases and the potential difference between the SENSE pin and GND drops below VLIM, the IC returns to normal operation.
If the slope of the inductor current is large, the delay time of the overcurrent protection circuit may cause an apparent increase in the potential difference between the SENSE pin and GND. This tends to occur when an inductor with low inductance is used or when VIN is large.

## 10. Frequency foldback function

The frequency foldback function has FB pin voltage ( $\mathrm{V}_{\mathrm{FB}}$ ) and oscillation frequency (fosc) to have a proportional relation when $V_{F B}$ is 0.7 V typ. or lower.
The frequency foldback function in this IC is set to invalid at start-up.

## 11. Short-circuit protection function

## 11. 1 Hiccup control

A / C type of this IC has a built-in short-circuit protection function for Hiccup control.
The hiccup control is a method for periodically carrying out automatic recovery when the IC detects overcurrent and stops the switching operation.

## 11. 1. 1 When overload status is released

<1> Overcurrent detection
$<2>$ After detection of the FB pin voltage $\left(\mathrm{V}_{\mathrm{FB}}\right)<0.7 \mathrm{~V}$ typ., frequency foldback function becomes valid.
$<3>$ Detection of $\mathrm{V}_{\mathrm{FB}}<0.5 \mathrm{~V}$ typ.
<4> 0.3 ms elapse
<5> Switching operation stop (for 21 ms typ.) (short-circuit protection detection status)
<6> Overload status release
<7> The IC restarts, soft-start function starts.
In this case, it is unnecessary to input an external reset signal for restart.
<8> $V_{\text {FB }}$ reaches 0.72 V typ. after 5.8 ms typ. elapses.


Figure 8

## 11. 1.2 When overload status continues

<1> Overcurrent detection
<2> After detection of $\mathrm{V}_{\mathrm{FB}}<0.7 \mathrm{~V}$ typ., frequency foldback function becomes valid.
$<3>$ Detection of $\mathrm{V}_{\mathrm{FB}}<0.5 \mathrm{~V}$ typ.
<4> 0.3 ms elapse
<5> Switching operation stop (for 21 ms typ.) (short-circuit protection detection status)
<6> The IC restarts, soft-start function starts.
$<7>$ The status returns to <3> when overload status continues after 8.6 ms typ. elapses.


Figure 9

### 11.2 Latch control

B / D type of this IC has a built-in short-circuit protection function for Latch control.
The latch control is a method for maintaining the Latch status when the IC detects overcurrent and stops the switching operation.
<1> Overcurrent detection
<2> After detection of $\mathrm{V}_{\mathrm{FB}}<0.7 \mathrm{~V}$ typ., frequency foldback function becomes valid.
$<3>$ Detection of $\mathrm{V}_{\mathrm{FB}}<0.5 \mathrm{~V}$ typ.
<4> 0.3 ms elapse
<5> Switching operation stop (short-circuit protection detection status)


Figure 10
In addition, Latch status is reset under the following conditions.

- At UVLO detection
- When the EN pin changes from "H" to "L".


## 12. Pre-bias compatible soft-start function

This IC has a built-in pre-bias compatible soft-start circuit.
If the pre-bias compatible soft-start circuit starts when electrical charge remains in the output voltage (Vout) as a result of power supply restart, etc., or when Vout is biased beforehand (pre-bias status), switching operation is stopped until the soft-start voltage exceeds the FB pin voltage ( $\mathrm{V}_{\mathrm{FB}}$ ), and then Vout is maintained. If the soft-start voltage exceeds $\mathrm{V}_{\mathrm{FB}}$, switching operation will restart and Vout will rise to the output voltage setting value. This allows the output voltage setting value to be reached without lowering the pre-biased Vout.

In this IC, Vout reaches the output voltage setting value gradually due to the soft-start circuit. In the following cases, rush current and Vout overshoot are reduced.

- When the EN pin changes from "L" to "H".
- When UVLO operation is released. ${ }^{* 1}$
- When thermal shutdown is released. ${ }^{* 1}$
- When recovering from short-circuit protection detection status*1
*1. In this case, the soft-start wait time is eliminated.
The soft-start circuit starts operating after " H " is input to the EN pin and the soft-start wait time (tssw) $=0.37 \mathrm{~ms}$ typ. elapses. The soft-start time (tss) is set to 5.8 ms typ.


Figure 11

## 13. Internal power supply ( $\mathrm{V}_{\mathrm{REG}}$ )

Some of the circuits in the IC operate using the VREG pin voltage ( $\mathrm{V}_{\text {REG }}$ ) as the power supply. To stabilize this internal power supply, a ceramic capacitor with $1 \mu \mathrm{~F}$ needs to be connected between the VREG pin and the VSS pin. To achieve low impedance, this capacitor should be placed as close to the IC as possible. Additionally, note that any external parts other than CREG or any load must not connect to the VREG pin.

## Typical Circuits

## 1. Step-up controller configuration


*1. $\mathrm{C}_{\mathrm{IN} 1}$ is a capacitor for stabilizing the input. If operation is unstable, add a capacitor in parallel.
*2. CIN2 is a bypass capacitor for stabilizing the IC operation. Connect it to the area nearest the VIN pin.
*3. Cout1 and Cout2 are capacitors for stabilizing the output. If operation is unstable, add a capacitor in parallel.
*4. RsF and CsF are RC filters to prevent FET switching noise from propagating to the SENSE pin.
*5. $\mathrm{C}_{\mathrm{HF}}$ is a high-frequency noise blocking capacitor to prevent malfunctions caused by switching noise.
Figure 12

## 2. Bootstrap configuration


*1. $\mathrm{C}_{\mathrm{IN} 1}$ is a capacitor for stabilizing the input. If operation is unstable, add a capacitor in parallel.
*2. $\mathrm{C}_{\mathrm{IN} 2}$ is a bypass capacitor for stabilizing the IC operation. Connect it to the area nearest the VIN pin.
*3. Cout1 and Cout2 are capacitors for stabilizing the output. If operation is unstable, add a capacitor in parallel.
*4. RSF and CsF are RC filters to prevent FET switching noise from propagating to the SENSE pin.
*5. $\mathrm{C}_{\mathrm{HF}}$ is a high-frequency noise blocking capacitor to prevent malfunctions caused by switching noise.
Figure 13

AUTOMOTIVE, $125^{\circ} \mathrm{C}$ OPERATION, 36 V INPUT, STEP-UP / FLYBACK SWITCHING REGULATOR CONTROLLER

## ■ External Parts Selection

Figure 12 shows a typical circuit based on our evaluation. Table 10 shows its operating conditions and Table 11 shows its external component constants.
If the input voltage $\left(\mathrm{V}_{\mathrm{IN}}\right)$ is lower than the VREG pin output voltage ( $\mathrm{V}_{\text {REG }}$ ), a bootstrap configuration (Figure 13) is recommended. Such a configuration will maintain $V_{\text {REG }}$ at 5 V and reduce FET ON-resistance. Also, at a frequency of 2.2 MHz, the FET losses will increase, and the FET may be damaged. Measure FET surface temperature during standard circuit operation to ensure that there is a margin for the maximum junction temperature rating.

Table 10 Design Example

| Design Parameter |  |
| :--- | :---: |$\quad$ Value

Table 11 Constants for External Components

| Symbol | Value | Quantity | Part Number | Manufacturer |
| :---: | :---: | :---: | :---: | :---: |
| L | $0.47 \mu \mathrm{H}$ | 1 | SPM5030VT-R47M-D | TDK Corporation |
| FET | - | 1 | IPC50N04S5L-5R5 | Infineon Technologies |
| D | - | 1 | PMEG045V100EPD | Nexperia B.V. |
| $\mathrm{C}_{\text {IN1 }}$ | $33 \mu \mathrm{~F}$ | 2 | GYC1H330MCQ1GS | NICHICON CORPORATION |
| $\mathrm{C}_{1 \mathrm{~N} 2}$ | $0.1 \mu \mathrm{~F}$ | 1 | CGA4J2X8R1H104K | TDK Corporation |
| Cout1 | $100 \mu \mathrm{~F}$ | 3 | GYC1H101MCQ1GS | NICHICON CORPORATION |
| Cout2 | $10 \mu \mathrm{~F}$ | 1 | CGA5L1X7R1H106K | TDK Corporation |
| $\mathrm{R}_{\text {gate }}$ | $10 \Omega$ | 1 | MCR3 series (1608) | ROHM CO., LTD. |
| RSENSE | $4 \mathrm{~m} \Omega$ | 1 | TLR2BPDTD4L00F75 | KOA CORPORATION |
| Rsf | $22 \Omega$ | 1 | MCR3 series (1608) | ROHM CO., LTD. |
| $\mathrm{C}_{\text {SF }}$ | 10 nF | 1 | CGA3E2X8R1H103K | TDK Corporation |
| $\mathrm{C}_{\text {Reg }}$ | $1 \mu \mathrm{~F}$ | 1 | CGA5L3X8R1H105K | TDK Corporation |
| Rcomp | $12 \mathrm{k} \Omega$ | 1 | MCR3 series (1608) | ROHM CO., LTD. |
| Ссомp | 4.7 nF | 1 | CGA3E2X8R1H472K | TDK Corporation |
| $\mathrm{C}_{\mathrm{HF}}$ | 220 pF | 1 | CGA3E2NP01H221J | TDK Corporation |
| $\mathrm{R}_{\text {FB1 }}$ | $200 \mathrm{k} \Omega+24 \mathrm{k} \Omega$ | 1 | MCR3 series (1608) | ROHM CO., LTD. |
| RFB2 | $16 \mathrm{k} \Omega$ | 1 | MCR3 series (1608) | ROHM CO., LTD. |

Caution The connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

## Board Layout Guidelines

Note the following cautions when determining the board layout for this IC.

- Place $\mathrm{C}_{\mathrm{IN}}(\mathrm{C} 10)$ as close to the VIN pin and the VSS pin as possible. Prioritize the layout of $\mathrm{C}_{\mathrm{IN}}$.
- Place Creg (C11) as close to the VREG pin and the VSS pin as possible. $_{\text {(Cle }}$
- Make the wiring of the FB pin as short as possible. Do not place it near a noise source.
- Make the switching loop composed of Cout (C13 to C19) $\rightarrow \mathrm{D} \rightarrow \mathrm{FET} \rightarrow$ RSEnSE $\rightarrow$ Cout (C13 to C19) as small as possible. This measure effectively reduces inductive high-frequency noise.
- The switching node (SW1) wiring area (Dashed line area in "Figure 14 Reference Board Pattern") should be as small as possible to reduce high-frequency radiation noise.
- Place Rsense close to the FET source.


Figure 14 Reference Board Pattern

Caution The above pattern diagram does not guarantee successful operation. Perform thorough evaluation using the actual application to determine the pattern.

## ■ Related Source

Refer to the following application note for external parts selection and board layout for this IC.

## S-19980/19990 Series EXTERNAL PARTS SELECTION Application Note

Refer to the following application note for flyback converter circuit using this IC.

## S-19980/19990 Series FLYBACK CONVERTER CIRCUIT Application Note

## ■ Precautions

- Mount external capacitors and inductors as close as possible to the IC, and make single GND.
- Characteristic ripple voltage and spike noise occur in the IC containing switching regulators. Moreover rush current flows at the time of a power supply injection. Because these largely depend on the inductor, the capacitor and impedance of power supply to be used, fully check them using an actually mounted model.
- The $0.1 \mu \mathrm{~F}$ capacitor ( $\mathrm{C}_{\mathrm{I} \mathrm{N} 2}$ in Figure 12, Figure 13) connected between the VIN pin and the VSS pin is a bypass capacitor. It stabilizes the power supply in the IC, and thus effectively works for stable switching regulator operation. Allocate the bypass capacitor as close to the IC as possible, prioritized over other parts.
- Although the IC contains a static electricity protection circuit, static electricity or voltage that exceeds the limit of the protection circuit should not be applied.
- The power dissipation of the IC greatly varies depending on the size and material of the board to be connected. Perform sufficient evaluation using an actual application before designing.
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## ■ Characteristics (Typical Data)

1. Example of major power supply dependence characteristics ( $\mathrm{Ta}=+25^{\circ} \mathrm{C}$ )
2. 1 Current consumption during switching off (Iss) vs. Input voltage (Viv)
3. 4. 1 S-19980 Series A/B type

1. 2 Current consumption during shutdown (Isss) vs. Input voltage ( $\mathrm{V}_{\mathrm{IN}}$ )

2. 3. 2 S-19980 Series C/D type

1. 3 FB pin voltage $\left(\mathrm{V}_{\mathrm{FB}}\right)$ vs. Input voltage ( $\mathrm{V}_{\mathrm{IN}}$ )

2. 4 Oscillation frequency (fosc) vs. Input voltage ( $\mathrm{V}_{\mathrm{IN}}$ )
1.4.1 S-19980 Series A/B type

1.4.2 S-19980 Series C/D type

3. 5 Soft-start wait time (tssw) vs. Input voltage (ViN)

4. 6 Soft-start time (tss) vs. Input voltage (Vin)


1.9 Overcurrent protection detection voltage (VLIM) vs. Input voltage ( $\mathrm{V}_{\mathrm{IN}}$ )

5. 11 Low level input voltage (VsL) vs. Input voltage (VIN)

1.8 GATE pin ON-resistance (Ronl)
vs. Input voltage (VIN)

6. 10 High level input voltage ( $\mathrm{V}_{\mathrm{sh}}$ ) vs. Input voltage (Vin)

1.12 Error amplifier transconductance (gm)
vs. Input voltage (Vin)

7. Example of major temperature characteristics ( $\mathrm{Ta}=-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ )
8. 1 Current consumption during switching off (Iss) vs. Temperature (Ta)
9. 10. 1 S-19980 Series A/B type

1. 2 Current consumption during shutdown (Isss) vs. Temperature (Ta)

2. 3. 2 S-19980 Series C/D type

1. 3 FB pin voltage ( $\mathrm{V}_{\mathrm{FB}}$ ) vs. Temperature ( Ta )

2. 4 Oscillation frequency (fosc) vs. Temperature (Ta)
3. 4. 1 S-19980 Series A/B type

1. 4. 2 S-19980 Series C / D type


## 2. 5 UVLO detection voltage (VuvLo-) vs. Temperature (Ta)


2. 7 Soft-start wait time (tssw) vs. Temperature (Ta)

2. 9 GATE pin ON-resistance (Ronн)
vs. Temperature (Ta)

2. 6 UVLO release voltage (VuvLO+) vs. Temperature (Ta)

2. 8 Soft-start time (tss) vs. Temperature ( Ta )

2. 10 GATE pin ON-resistance (Ronl)
vs. Temperature (Ta)

2. 11 Overcurrent protection detection voltage (VLIM) vs. Temperature (Ta)

2. 13 Low level input voltage (VsL) vs. Temperature ( Ta )

2. 12 High level input voltage ( $\mathrm{V}_{\mathrm{SH}}$ )
vs. Temperature ( Ta )

2. 14 Error amplifier transconductance (gm) vs. Temperature (Ta)

3. EN pin characteristics $\left(\mathrm{Ta}=+25^{\circ} \mathrm{C}\right)$
3. 1 High level input current (Ish) vs. EN pin voltage (VEN)


## 4. Transient response characteristics

The external parts shown in Table 12 are used in "4. Transient response characteristics".
Table 12

| Symbol | Value | Part Number | Manufacturer |
| :---: | :---: | :---: | :---: |
| L | A / B type: $0.47 \mu \mathrm{H}$ | SPM5030VT-R47M-D | TDK Corporation |
|  | C / D type: $1.5 \mu \mathrm{H}$ | SPM12565VT-1R5M-D | TDK Corporation |
| FET | - | IPC50N04S5L-5R5 | Infineon Technologies |
| D | - | PMEG045V100EPD | Nexperia B.V. |
| $\mathrm{Cl}_{\text {IN1 }}$ | $33 \mu \mathrm{~F}$ | GYC1H330MCQ1GS | NICHICON CORPORATION |
| CIN2 | $0.1 \mu \mathrm{~F}$ | CGA4J2X8R1H104K | TDK Corporation |
| Cout1 | $100 \mu \mathrm{~F}$ | GYC1H101MCQ1GS | NICHICON CORPORATION |
| Cout2 | $10 \mu \mathrm{~F}$ | CGA5L1X7R1C106K | TDK Corporation |

4. 1 Power-on ( $\mathrm{V}_{\text {OUt }}=12 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{EN}}=0 \mathrm{~V} \rightarrow 6 \mathrm{~V}, \mathrm{Ta}=+25^{\circ} \mathrm{C}$ )

## 4. 1. 1 S-19980 Series A/B type


4. 1. 2 S-19980 Series C/D type
(1) lоит $=1 \mathrm{~mA}$

(2) lout $=1 \mathrm{~A}$

4. 2 Transient response characteristics of EN pin (Vout $=12 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=\mathbf{6} \mathrm{V}, \mathrm{V}_{\mathrm{EN}}=0 \mathrm{~V} \rightarrow 2.0 \mathrm{~V}, \mathrm{Ta}=+25^{\circ} \mathrm{C}$ )
4. 2. 1 S-19980 Series A/B type
(1) lout $=1 \mathrm{~mA}$

(2) lout $=1 \mathrm{~A}$

4. 2. 2 S-19980 Series C/D type

4. 3 Line transient response ( $\mathrm{V}_{\text {OUt }}=12 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=6 \mathrm{~V} \rightarrow 9 \mathrm{~V} \rightarrow 6 \mathrm{~V}, \mathrm{Ta}=+25^{\circ} \mathrm{C}$ )

## 4. 3. 1 S-19980 Series A/B type

(1) lout $=1 \mathrm{~mA}$


4. 3. 2 S-19980 Series C / D type

(2) lout $=500 \mathrm{~mA}$

4. 4 Load transient response ( $\mathrm{V}_{\text {OUt }}=12 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=6 \mathrm{~V}, \mathrm{Ta}=+25^{\circ} \mathrm{C}$ )

## 4. 4. 1 S-19980 Series A/B type

(1) lоит $=10 \mathrm{~mA} \rightarrow \mathbf{5 0 0} \mathrm{~mA} \rightarrow 10 \mathrm{~mA}$


(2) lout $=10 \mathrm{~mA} \rightarrow 1000 \mathrm{~mA} \rightarrow 10 \mathrm{~mA}$


## 4. 4. 2 S-19980 Series C/D type



## ■ Reference Data

The external parts shown in Table 13 are used in "■ Reference Data".

Table 13

| Condition | Symbol | Value | Quantity | Part Number | Manufacturer |
| :---: | :---: | :---: | :---: | :---: | :---: |
| <1> | L | $1.5 \mu \mathrm{H}$ | 1 | SPM12565VT-1R5M-D | TDK Corporation |
|  | FET | - | 1 | IPC50N04S5L-5R5 | Infineon Technologies |
|  | D | - | 1 | PMEG045V100EPD | Nexperia B.V. |
|  | $\mathrm{Cin}^{\text {N }}$ | $0.1 \mu \mathrm{~F}$ | 1 | CGA4J2X8R1H104K | TDK Corporation |
|  |  | $33 \mu \mathrm{~F}$ | 2 | GYC1H330MCQ1GS | NICHICON CORPORATION |
|  | Cout | $10 \mu \mathrm{~F}$ | 2 | CGA5L1X7R1C106K | TDK Corporation |
|  |  | $100 \mu \mathrm{~F}$ | 3 | GYC1H101MCQ1GS | NICHICON CORPORATION |
| <2> | L | $0.47 \mu \mathrm{H}$ | 1 | SPM5030VT-R47M-D | TDK Corporation |
|  | FET | - | 1 | IPC50N04S5L-5R5 | Infineon Technologies |
|  | D | - | 1 | PMEG045V100EPD | Nexperia B.V. |
|  | $\mathrm{Cin}_{\text {I }}$ | $0.1 \mu \mathrm{~F}$ | 1 | CGA4J2X8R1H104K | TDK Corporation |
|  |  | $33 \mu \mathrm{~F}$ | 2 | GYC1H330MCQ1GS | NICHICON CORPORATION |
|  | Cout | $10 \mu \mathrm{~F}$ | 2 | CGA5L1X7R1C106K | TDK Corporation |
|  |  | $100 \mu \mathrm{~F}$ | 3 | GYC1H101MCQ1GS | NICHICON CORPORATION |

1. Vout $=12 \mathrm{~V}$ (External parts: Condition <1>)

## 1. 1 S-19980 Series C / D type

1.1.1 Efficiency $(\eta)$ vs. Output current (lout)


1. 2. 2 Output voltage (VOUT) vs. Output current (IOUT)

1.1.3 Ripple voltage ( $\Delta \mathrm{V}_{\text {out }}$ ) vs. Output current (lout)

1. Vout $=12$ V (External parts: Condition <2>)

## 2. 1 S-19980 Series A/B type


2. 1.3 Ripple voltage ( $\Delta \mathrm{V}$ оut) vs. Output current (Iout)

3. Vout $=9.5$ V (External parts: Condition <1>)
3. 1 S-19980 Series C / D type
3. 1. 1 Efficiency $(\eta)$ vs. Output current (lout)

3. 1. 2 Output voltage (Vout) vs. Output current (lout)

3. 1. 3 Ripple voltage ( $\Delta$ Vout) vs. Output current (lout)

4. $\mathrm{V}_{\text {оиt }}=9.5 \mathrm{~V}$ (External parts: Condition <2>)
4. 1 S-19980 Series A/B type

4. 1. 3 Ripple voltage ( $\Delta$ Vout) vs. Output current (lout)

5. Load dump characteristics ( $\mathrm{Ta}=+25^{\circ} \mathrm{C}$ )
5. $1 \quad V_{\text {оut }}=12 \mathrm{~V}$


## ■ Power Dissipation

HTMSOP-8


| Board | Power Dissipation (PD) |
| :---: | :---: |
| A | 0.79 W |
| B | 1.11 W |
| C | 3.21 W |
| D | 3.13 W |
| E | 4.17 W |

HSNT-8(2030)


| Board | Power Dissipation (PD) |
| :---: | :---: |
| A | 0.69 W |
| B | 0.93 W |
| C | 3.13 W |
| D | 2.98 W |
| E | 3.91 W |

## HTMSOP-8 Test Board

(1) Board A

IC Mount Area


| Item |  | Specification |
| :---: | :---: | :---: |
| Size [mm] |  | $114.3 \times 76.2 \times \mathrm{t} 1.6$ |
| Material |  | FR-4 |
| Number of copper foil layer |  | 2 |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: 0.070 |
|  | 2 | - |
|  | 3 | - |
|  | 4 | $74.2 \times 74.2 \times$ t0.070 |
| Thermal via |  | - |

(2) Board B


| Item | Specification |  |  |
| :--- | :--- | :--- | :---: |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t1} .6$ |  |  |
| Material | FR-4 |  |  |
| Number of copper foil layer | 4 |  |  |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |  |
|  | 2 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |  |
|  | 3 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |  |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t0.070}$ |  |
| Thermal via |  |  |  |

(3) Board C


| Item | Specification |  |
| :--- | ---: | :--- |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t} 1.6$ |  |
| Material | FR-4 |  |
| Number of copper foil layer | 4 |  |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
|  | 2 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 3 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t0.070}$ |
| Thermal via | Number: 4 <br> Diameter: 0.3 mm |  |

enlarged view
No. HTMSOP8-A-Board-SD-1.0

## HTMSOP-8 Test Board

## (5) Board E



| Item | Specification |  |
| :--- | :--- | :--- |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t} 1.6$ |  |
| Material | FR-4 |  |
| Number of copper foil layer | 4 |  |
| Copper foil layer $[\mathrm{mm}]$ | 1 | Pattern for heat radiation: $2000 \mathrm{~mm}^{2}$ t0.070 |
|  | 2 | $74.2 \times 74.2 \times \mathrm{t} 0.035$ |
|  | 3 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t0.070}$ |
| Thermal via |  | Number: 4 <br> Diameter: 0.3 mm |


| Item | Specification |  |  |  |
| :--- | :--- | :--- | :---: | :---: |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t} 1.6$ |  |  |  |
| Material | FR-4 |  |  |  |
| Number of copper foil layer | 4 |  |  |  |
| Copper foil layer [mm] | 1 | Pattern for heat radiation: $2000 \mathrm{~mm}^{2}$ t0.070 |  |  |
|  | 2 | $74.2 \times 74.2 \times \mathrm{t} 0.035$ |  |  |
|  | 3 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |  |  |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t} 0.070$ |  |  |
| Thermal via |  |  |  |  |


enlarged view

No. HTMSOP8-A-Board-SD-1.0

## (1) Board A



| Item | Specification |  |
| :--- | :---: | :--- |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t1.6}$ |  |
| Material | FR-4 |  |
| Number of copper foil layer | 2 |  |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
|  | 2 | - |
|  | 3 | - |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t0.070}$ |
| Thermal via |  |  |

(2) Board B


| Item | Specification |  |
| :--- | :---: | :--- |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t1.6}$ |  |
| Material | FR-4 |  |
| Number of copper foil layer | 4 |  |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
|  | 2 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 3 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t} 0.070$ |
| Thermal via |  |  |

## (3) Board C



| Item | Specification |  |
| :--- | :--- | :--- |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t} 1.6$ |  |
| Material | FR-4 |  |
| Number of copper foil layer | 4 |  |
| Copper foil layer [mm] | 1 | Land pattern and wiring for testing: t0.070 |
|  | 2 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 3 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t0.070}$ |
| Thermal via | Number: 4 <br> Diameter: 0.3 mm |  |

No. HSNT8-A-Board-SD-2.0

ABLIC Inc.
(4) Board D


| Item |  | Specification |
| :---: | :---: | :---: |
| Size [mm] |  | $114.3 \times 76.2 \times$ t1.6 |
| Material |  | FR-4 |
| Number of copper foil layer |  | 4 |
| Copper foil layer [mm] | 1 | Pattern for heat radiation: $2000 \mathrm{~mm}^{2}$ t0.070 |
|  | 2 | $74.2 \times 74.2 \times$ t0.035 |
|  | 3 | $74.2 \times 74.2 \times$ t0.035 |
|  | 4 | $74.2 \times 74.2 \times$ t0.070 |
| Thermal via |  | - |


enlarged view

## (5) Board E



| Item | Specification |  |
| :--- | :---: | :--- |
| Size $[\mathrm{mm}]$ | $114.3 \times 76.2 \times \mathrm{t} 1.6$ |  |
| Material | FR-4 |  |
| Number of copper foil layer | 4 |  |
| Copper foil layer $[\mathrm{mm}]$ | 1 | Pattern for heat radiation: $2000 \mathrm{~mm}^{2}$ t0.070 |
|  | 2 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 3 | $74.2 \times 74.2 \times \mathrm{t0.035}$ |
|  | 4 | $74.2 \times 74.2 \times \mathrm{t0.070}$ |
| Thermal via |  |  |

enlarged view

No. HSNT8-A-Board-SD-2.0


No. FP008-A-P-SD-2.0

| TITLE | HTMSOP8-A-PKG Dimensions |
| :---: | :---: |
| No. | FP008-A-P-SD-2.0 |
| ANGLE | $\rightarrow$ |
| UNIT | mm |
|  |  |
|  |  |
| ABLIC Inc. |  |



No. FP008-A-C-SD-1.0

| TITLE | HTMSOP8-A-Carrier Tape |
| :---: | :---: |
| No. | FP008-A-C-SD-1.0 |
| ANGLE |  |
| UNIT | mm |
|  |  |
|  |  |
| ABLIC Inc. |  |



Enlarged drawing in the central part


No. FP008-A-R-SD-2.0

| TITLE | HTMSOP8-A-Reel |  |
| :---: | :---: | :---: |
| No. | FP008-A-R-SD-2.0 |  |
| ANGLE |  |  |
| UNIT | mm | QTY. |
|  | 4,000 |  |
|  |  |  |
| ABLIC Inc. |  |  |



No. FP008-A-L-SD-2.0

| TITLE | HTMSOP8-A <br> -Land Recommendation |
| :---: | :---: |
| No. | FP008-A-L-SD-2.0 |
| ANGLE |  |
| UNIT | mm |
|  |  |
|  |  |
| ABLIC Inc. |  |


※ The heat sink of back side has different electric potential depending on the product.
Confirm specifications of each product.
Do not use it as the function of electrode.
No. PP008-A-P-SD-2.0

| TITLE | HSNT-8-A-PKG Dimensions |
| :---: | :---: |
| No. | PP008-A-P-SD-2.0 |
| ANGLE | $\square$ |
| UNIT | mm |
|  |  |
|  |  |
| ABLIC Inc. |  |



Feed direction

No. PP008-A-C-SD-1.0

| TITLE | HSNT-8-A-Carrier Tape |
| :---: | :---: |
| No. | PP008-A-C-SD-1.0 |
| ANGLE |  |
| UNIT | mm |
|  |  |
|  |  |
| ABLIC Inc. |  |



## Enlarged drawing in the central part



No. PP008-A-R-SD-2.0

| TITLE | HSNT-8-A-Reel |  |
| :---: | :---: | :---: |
| No. | PP008-A-R-SD-2.0 |  |
| ANGLE | QTY. |  |
| UNIT | mm |  |
|  |  |  |
|  |  |  |
| ABLIC Inc. |  |  |



No. PP008-A-L-SD-1.0

| TITLE | HSNT-8-A <br> -Land Recommendation |
| :---: | :---: |
| No. | PP008-A-L-SD-1.0 |
| ANGLE |  |
| UNIT | mm |
|  |  |
|  |  |
| ABLIC Inc. |  |

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